

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A semiconductor device comprising:

a semiconductor substrate including a source region and drain region at its surface;

a gate electrode formed so as to include a straight portion separating said source region and said drain region on said semiconductor substrate;

a dummy electrode formed at a position on an extension of a longitudinal axis of said gate electrode;

a stopper insulating film, each overlying said gate electrode and said dummy electrode;

a sidewall insulating film covering a side of said gate electrode, said dummy electrode and said stopper insulating film;

an interlayer insulating film formed on said semiconductor substrate to cover up said sidewall insulating film and said stopper insulating film; and

a linear contact portion defined by a conductive member extending vertically in said interlayer insulating film and electrically connected to one of said source region and said drain region at its bottom end, said linear contact portion extending parallel to said straight portion of said gate electrode, said linear contact portion extending to above said dummy electrode;

wherein a gap between said gate electrode and said dummy electrode is filled with said sidewall insulating film.

2. (Previously presented) A semiconductor device comprising:

a semiconductor substrate including a source region and drain region at its surface;

a gate electrode formed so as to include a straight portion separating said source region and said drain region on said semiconductor substrate;

a dummy electrode formed at a position on an extension of a longitudinal direction of said gate electrode;

a stopper insulating film, each overlying said gate electrode and said dummy electrode;

a sidewall insulating film covering a side of said gate electrode, said dummy electrode and said stopper insulating film;

an interlayer insulating film formed on said semiconductor substrate to cover up said sidewall insulating film and said stopper insulating film; and

a linear contact portion defined by a conductive member extending vertically in said interlayer insulating film and electrically connected to one of said source region and said drain region at its bottom end, said linear contact portion extending parallel to said straight portion of said gate electrode, said linear contact portion extending to above said dummy electrode;

wherein, in a plan view, each longer side of a rectangle defined by said linear contact portion is located beyond said sidewall insulating film and within a top region of said gate electrode and said dummy electrode, and

a gap between said gate electrode and said dummy electrode is filled with said sidewall insulating film.

3. (Previously Presented) A semiconductor device comprising:

a semiconductor substrate including a source region and drain region at its surface;

a gate electrode formed so as to include a straight portion separating said source region and said drain region on said semiconductor substrate;

a dummy electrode formed at a position on an extension of a longitudinal direction of said gate electrode;

a stopper insulating film, each overlying said gate electrode and said dummy electrode;

a sidewall insulating film covering a side of said gate electrode, said dummy electrode and said stopper insulating film;

an interlayer insulating film formed on said semiconductor substrate to cover up said sidewall insulating film and said stopper insulating film; and

a linear contact portion defined by a conductive member extending vertically in said interlayer insulating film and electrically connected to one of said source region and said drain region at its bottom end, said linear contact portion extending parallel to said straight portion of said gate electrode, said linear contact portion extending to above said dummy electrode;

wherein said gate electrode is arranged in plurality parallel to each other and one of said source region and said drain region constitutes a group of regions of a specified type defined in regions between adjacent two of said gate electrodes being discrete with an isolation insulating film therebetween, and said linear contact portion extends to integrally cover said group of regions of the specified type.

4. (Previously Presented) The semiconductor device of claim 3, wherein said one of said source region and said drain region is electrically connected, via said linear contact portion, to a first interconnection extending, above said linear contact portion, parallel to said straight portion, and the other one of said source region and said drain region is electrically connected to a second interconnection extending, above said gate electrode, transversely to said straight portion of said gate electrode.

5. (New) A semiconductor device comprising:

a semiconductor substrate;

an isolation insulating film region formed on a surface of said semiconductor substrate and extending in a first direction;

an active region sectioned by said isolation insulating film and extending in said first direction;

a gate electrode extending in a second direction traversing said active region;

a dummy electrode disposed at that end of said gate electrode on an extension of said second direction;

a first contact portion extending in said second direction along said gate electrode; and

first and second sidewall insulating films deposited on side surfaces of said gate and dummy electrodes, respectively, wherein:

said first contact portion extends to and above said dummy electrode; and

a gap between said gate and dummy electrodes is filled with said first and second sidewall insulating films continuously.

6. (New) The semiconductor device according to claim 5, further comprising:

a stopper insulating film overlapping upper sides of said gate and dummy electrodes, respectively; and

an interlayer insulating film overlying said semiconductor substrate to cover said stopper and sidewall insulating films.

7. (New) The semiconductor device according to claim 5, more than one said gate electrode being provided in said second direction in parallel, further comprising source and drain regions formed on said active region between said gate electrodes.

8. (New) The semiconductor device according to claim 7, wherein one of a group of said source regions and that of said drain regions has its regions in a region sandwiched between adjacent ones of said gate electrodes such that said regions are spaced by an isolation insulating film and aligned with each other.

9. (New) The semiconductor device according to claim 5, wherein said first contact portion as seen in said second direction has a side located beyond said first and second sidewall insulating films and within a top region of said gate electrode.

10. (New) The semiconductor device according to claim 5, wherein said gate electrode includes a floating gate and a control gate electrode disposed on said floating gate electrode with an insulating film posed therebetween.

11. (New) The semiconductor device according to claim 5, wherein said dummy electrode does not electrically affect the semiconductor device in function.

12. (New) The semiconductor device according to claim 5, further comprising:
a second contact portion provided at said interlayer insulating film;
a first interconnection electrically connected to said one said source and drain regions via said second contact portion, and overlying said interlayer insulating film and extending parallel to said second direction; and

a second interconnection electrically connected to the other of said source and drain regions via said first contact portion, and overlying said first interconnection and extending in said first direction.